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said first electrode layer including at least one selected from a first metal group of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group of Ni, Pd and Co, and

said third electrode layer including Au.

Subt B²
Please add the following claims:

8. (New) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer including at least one metal having a free energy of nitride formation of less -51 kcal/mol,

said second electrode layer including at least one selected from a second metal group of Ni, Pd and Co, and

a²
said third electrode layer including Au.

Sub D₁
9. (New) The electrode structure according to claim 8, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

10. (New) The electrode structure according to claim 8, wherein said second electrode layer has a thickness of 5 nm or more.

11. (New) The electrode structure according to claim 8, wherein said third electrode layer has a thickness of 50 nm or more.
